

SILICON POWER TRANSISTORS

Designed for use in automotive ignition, switching and motor control applications.

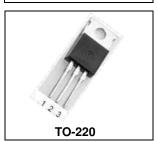
DESCRIPTION :

- Collector–Emitter Breakdown Voltage
- V_{(BR)CEO} = 400V(Min.)
- Collector Saturation Voltage
 - V_{CE}(sat) = 2.0V(Max) @ IC= 5.0A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

7 AMPERES
DARLINGTON
POWER TRANSISTOR
400 VOLTS
80 WATTS
00 WAT15

NPN

TIP152

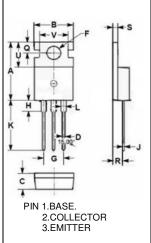


MAXIMUM RATINGS

Characteristic	Symbol	TIP152	Unit
Collector-Base Voltage	V _{CBO}	400	V
Collector-Emitter Voltage	V _{CEO}	400	V
Emitter-Base Voltage	V _{EBO}	8	V
Collector Current-Continuous	lc	7	А
Collector Current-Peak	I _{CM}	10	A
Base Current- Continuous	I _B	1.5	А
Collector Power Dissipation @T_c=25 $^\circ\!\!\mathbb{C}$	Pc	80	Watts
Junction Temperature	TJ	150	°C
Storage Temperature	T _{STG}	-65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R _{th j-c}	1.56	°C/W



DIM	MILLIMETERS			
	MIN	MAX		
Α	15.50	15.90		
В	9.80	10.20		
С	4.20	4.50		
D	0.70	0.90		
	3.40	3.70		
G	4.98	5.18		
Н	2.68	2.90		
J	0.44	0.60		
K	12.80	13.40		
L	1.20	1.45		
Q	2.70	2.90		
R	2.30	2.70		
S	1.29	1.35		
U	6.45	6.65		
V	8.66	8.86		

Characteristic	Symbol	Min.	Max	Unit
OFFCHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_c = 10 \text{ mA}, I_B = 0$)	V _{CEO}	400		v
Collector-Base Breakdown Voltage ($I_C = 1 \text{ mA}, I_E = 0$)	V _{CBO}	400		V
Collector Cutoff Current ($V_{CE} = 400 \text{ V}, I_B = 0$)	I _{CEO}		0.25	mA
Emitter Cutoff Current (V_{EB} = 8.0 V, I_{C} = 0)	I _{EBO}		15	mA
ON CHARACTERISTICS				
DC Current Gain (I _C = 2.5 A, V _{CE} = 5.0 V) (I _C = 5.0 A, V _{CE} = 5.0 V) (I _C = 7.0 A, V _{CE} = 5.0 V)	h _{FE}	150 50 15		
Collector-Emitter Saturation Voltage ($I_C = 1.0 \text{ A}, I_B = 10 \text{ mA}$) ($I_C = 2.0 \text{ A}, I_B = 100 \text{ mA}$) ($I_C = 5.0 \text{ A}, I_B = 250 \text{ mA}$)	V _{CE(sat)}		1.5 1.5 2.0	v
Base-Emitter Saturation Voltage ($I_C = 2 A$, $I_B = 100 mA$) ($I_C = 5 A$, $I_B = 250 mA$)	V _{BE(sat)}		2.2 2.3	v
Diode Forward Voltage (I _F = 7.0 A)	VF		3.5	V

DYNAMIC CHARATERISTICS

Collector Output Capacitance $(V_{CB}=10 \text{ V}, I_E=0, f=1.0 \text{ MHz})$	C _{Ob}		150	pF	
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